

EH35 45 ET

Series -RoHS Compliant (Pb-free) 5.0V 4 Pad 3.2mm x 5mm Ceramic SMD HCMOS/TTL High Frequency Oscillator

Frequency Tolerance/Stability ±50ppm Maximum

Operating Temperature Range --40°C to +85°C

### **ELECTRICAL SPECIFICATIONS**

Nominal Frequency	75.000MHz
Frequency Tolerance/Stability	±50ppm Maximum (Inclusive of all conditions: Calibration Tolerance at 25°C, Frequency Stability over the Operating Temperature Range, Supply Voltage Change, Output Load Change, 1st Year Aging at 25°C, Shock, and Vibration)
Aging at 25°C	±5ppm/year Maximum
Operating Temperature Range	-40°C to +85°C
Supply Voltage	5.0Vdc ±10%
Input Current	50mA Maximum (No Load)
Output Voltage Logic High (Voh)	2.4Vdc Minimum with TTL Load, Vdd-0.4Vdc Minimum with HCMOS Load (IOH = -16mA)
Output Voltage Logic Low (Vol)	0.4Vdc Maximum with TTL Load, 0.5Vdc Maximum with HCMOS Load (IOL = +16mA)
Rise/Fall Time	4nSec Maximum (Measured at 0.8Vdc to 2.0Vdc with TTL Load or at 20% to 80% of waveform with HCMOS Load)
Duty Cycle	50 $\pm$ 10(%) (Measured at 50% of waveform with TTL Load or with HCMOS Load)
Load Drive Capability	5TTL Load or 15pF HCMOS Load Maximum
Output Logic Type	CMOS
Pin 1 Connection	Tri-State (Disabled Output: High Impedance)
Tri-State Input Voltage (Vih and Vil)	+2.2Vdc Minimum to enable output, +0.8Vdc Maximum to disable output (High Impedance), No Connect to enable output.
Absolute Clock Jitter	±250pSec Maximum, ±100pSec Typical
One Sigma Clock Period Jitter	±50pSec Maximum, ±30pSec Typical
Start Up Time	10mSec Maximum
Storage Temperature Range	-55°C to +125°C
ENVIRONMENTAL & MEC	HANICAL SPECIFICATIONS
Fine Leak Test	MIL-STD-883, Method 1014, Condition A

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Gross Leak Test	MIL-STD-883, Method 1014, Condition C
Mechanical Shock	MIL-STD-202, Method 213, Condition C
Resistance to Soldering Heat	MIL-STD-202, Method 210
Resistance to Solvents	MIL-STD-202, Method 215
Solderability	MIL-STD-883, Method 2003
Temperature Cycling	MIL-STD-883, MEthod 1010
Vibration	MIL-STD-883, Method 2007, Condition A



-75.000M

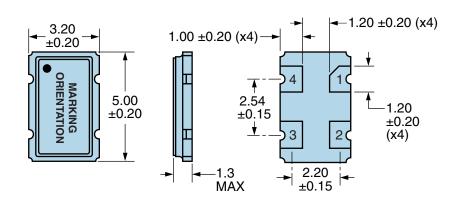
- Nominal Frequency 75.000MHz

- Pin 1 Connection

Tri-State (Disabled Output: High Impedance)

Duty Cycle 50 ±10(%)

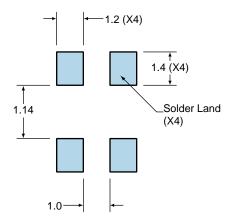
### **MECHANICAL DIMENSIONS (all dimensions in millimeters)**



PIN	CONNECTION
1	Tri-State
2	Ground/Case Ground
3	Output
4	Supply Voltage
LINE	MARKING
1	E75.000 E=Ecliptek Designator

### Suggested Solder Pad Layout

All Dimensions in Millimeters

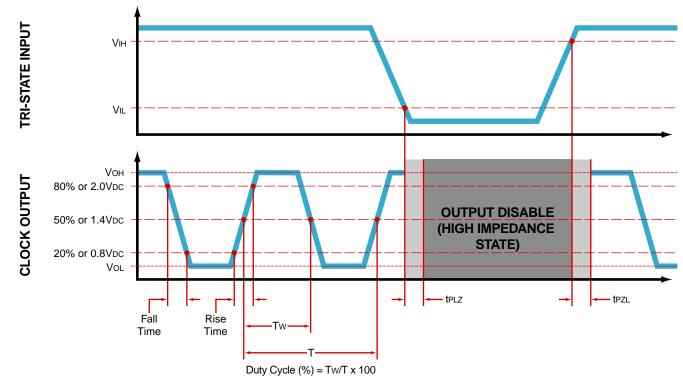


All Tolerances are ±0.1





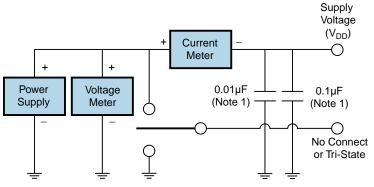
#### **OUTPUT WAVEFORM & TIMING DIAGRAM**

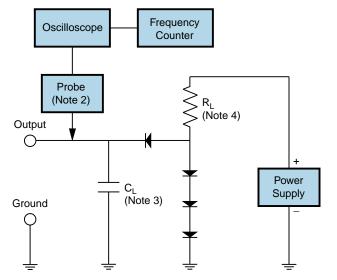


#### Test Circuit for TTL Output

Output Load Drive Capability	R <sub>L</sub> Value (Ohms)	C <sub>L</sub> Value (pF)
10TTL	390	15
5TTL	780	15
2TTL	1100	6
10LSTTL	2000	15
1TTL	2200	3







Note 1: An external 0.1µF low frequency tantalum bypass capacitor in parallel with a 0.01µF high frequency ceramic bypass capacitor close to the package ground and V<sub>DD</sub> pin is required.

Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth

(>300MHz) passive probe is recommended.

Note 3: Capacitance value  $C_L$  includes sum of all probe and fixture capacitance.

Note 4: Resistance value R<sub>L</sub> is shown in Table 1. See applicable specification sheet for 'Load Drive Capability'.

Note 5: All diodes are MMBD7000, MMBD914, or equivalent.



### **Test Circuit for CMOS Output**



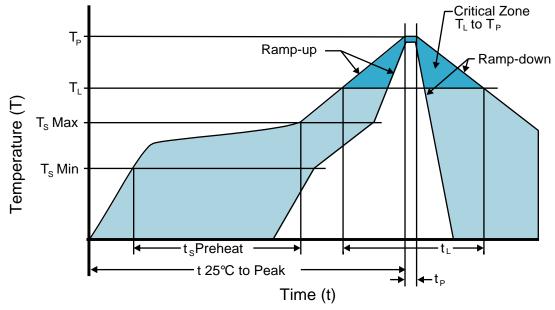
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# **Recommended Solder Reflow Methods**



### **High Temperature Infrared/Convection**

EH3545ETTS-75.000M

T <sub>s</sub> MAX to T <sub>L</sub> (Ramp-up Rate)	3°C/second Maximum
Preheat	
- Temperature Minimum (T <sub>s</sub> MIN)	150°C
- Temperature Typical (T <sub>s</sub> TYP)	175°C
- Temperature Maximum (T <sub>s</sub> MAX)	200°C
- Time (t <sub>s</sub> MIN)	60 - 180 Seconds
Ramp-up Rate (T⊾ to T <sub>P</sub> )	3°C/second Maximum
Time Maintained Above:	
- Temperature (T∟)	217°C
- Time (t <sub>L</sub> )	60 - 150 Seconds
Peak Temperature (T <sub>P</sub> )	260°C Maximum for 10 Seconds Maximum
Target Peak Temperature (T <sub>P</sub> Target)	250°C +0/-5°C
Time within 5°C of actual peak (t <sub>p</sub> )	20 - 40 seconds
Ramp-down Rate	6°C/second Maximum
Time 25°C to Peak Temperature (t)	8 minutes Maximum
Moisture Sensitivity Level	Level 1



## **Recommended Solder Reflow Methods**

EH3545ETTS-75.000M



## Low Temperature Infrared/Convection 240°C

T <sub>s</sub> MAX to T <sub>L</sub> (Ramp-up Rate)	Rate) 5°C/second Maximum	
Preheat		
- Temperature Minimum (Ts MIN)	N/A	
- Temperature Typical (T <sub>s</sub> TYP)	150°C	
- Temperature Maximum (T <sub>s</sub> MAX)	N/A	
- Time (t <sub>s</sub> MIN)	60 - 120 Seconds	
Ramp-up Rate (T⊾ to T <sub>P</sub> )	5°C/second Maximum	
Time Maintained Above:		
· Temperature (T∟)	150°C	
· Time (t∟)	200 Seconds Maximum	
Peak Temperature (T <sub>P</sub> )	240°C Maximum	
arget Peak Temperature (T <sub>P</sub> Target)	240°C Maximum 1 Time / 230°C Maximum 2 Times	
Fime within 5°C of actual peak (t <sub>ρ</sub> )	10 seconds Maximum 2 Times / 80 seconds Maximum 1 Time	
Ramp-down Rate	5°C/second Maximum	
Time 25°C to Peak Temperature (t)	N/A	
Moisture Sensitivity Level	Level 1	

#### Low Temperature Manual Soldering

185°C Maximum for 10 seconds Maximum, 2 times Maximum.

### **High Temperature Manual Soldering**

260°C Maximum for 5 seconds Maximum, 2 times Maximum.